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Kind regards,

Team Nexperia

PHP3055E

N-channel TrenchMOS standard level FET

Rev. 07 — 26 February 2010

Product data sheet

1. Product profile

1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

1.3 Applications

- DC-to-DC convertors
- Switched-mode power supplies

1.4 Quick reference data

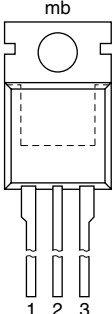
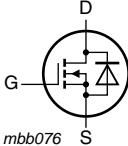
Table 1. Quick reference

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|--|-----|-----|------|------------|
| V_{DS} | drain-source voltage | $T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$ | - | - | 60 | V |
| I_D | drain current | $T_{mb} = 25\text{ °C}; V_{GS} = 10\text{ V};$ see Figure 1 and 3 | - | - | 10.3 | A |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ °C};$ see Figure 2 | - | - | 33 | W |
| Dynamic characteristics | | | | | | |
| Q_{GD} | gate-drain charge | $V_{GS} = 10\text{ V}; I_D = 10\text{ A};$ $V_{DS} = 44\text{ V}; T_j = 25\text{ °C};$ see Figure 12 | - | 3.2 | - | nC |
| Static characteristics | | | | | | |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 10\text{ V}; I_D = 5.5\text{ A};$ $T_j = 25\text{ °C};$ see Figure 10 and 11 | - | 120 | 150 | m Ω |



2. Pinning information

Table 2. Pinning information

| Pin | Symbol | Description | Simplified outline | Graphic symbol |
|-----|--------|-----------------------------------|--|---|
| 1 | G | gate |  |  |
| 2 | D | drain | | |
| 3 | S | source | | |
| mb | D | mounting base; connected to drain | | |

SOT78 (TO-220AB)

3. Ordering information

Table 3. Ordering information

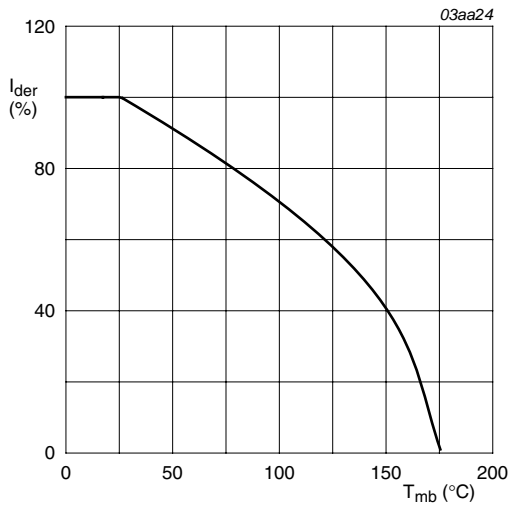
| Type number | Package | | Version |
|-------------|----------|--|---------|
| | Name | Description | |
| PHP3055E | TO-220AB | plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB | SOT78 |

4. Limiting values

Table 4. Limiting values

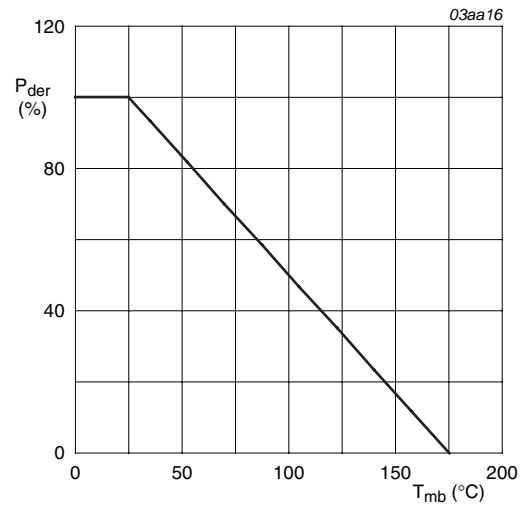
In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|-----------------------------|---|---|-----|------|------|
| V_{DS} | drain-source voltage | $T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}$ | - | 60 | V |
| V_{DGR} | drain-gate voltage | $T_j \geq 25\text{ °C}; T_j \leq 175\text{ °C}; R_{GS} = 20\text{ k}\Omega$ | - | 60 | V |
| V_{GS} | gate-source voltage | | -20 | 20 | V |
| I_D | drain current | $V_{GS} = 10\text{ V}; T_{mb} = 100\text{ °C}$; see Figure 1 | - | 7.3 | A |
| | | $V_{GS} = 10\text{ V}; T_{mb} = 25\text{ °C}$; see Figure 1 and 3 | - | 10.3 | A |
| I_{DM} | peak drain current | $t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$; see Figure 3 | - | 41 | A |
| P_{tot} | total power dissipation | $T_{mb} = 25\text{ °C}$; see Figure 2 | - | 33 | W |
| T_{stg} | storage temperature | | -55 | 175 | °C |
| T_j | junction temperature | | -55 | 175 | °C |
| Source-drain diode | | | | | |
| I_S | source current | $T_{mb} = 25\text{ °C}$ | - | 10.3 | A |
| I_{SM} | peak source current | $t_p \leq 10\text{ }\mu\text{s}$; pulsed; $T_{mb} = 25\text{ °C}$ | - | 41 | A |
| Avalanche ruggedness | | | | | |
| $E_{DS(AL)S}$ | non-repetitive drain-source avalanche energy | $V_{GS} = 10\text{ V}; T_{j(init)} = 25\text{ °C}; I_D = 3.3\text{ A}; V_{sup} \leq 25\text{ V}; R_{GS} = 50\text{ }\Omega$; unclamped; $t_p = 0.22\text{ ms}$ | - | 25 | mJ |
| $I_{DS(AL)S}$ | non-repetitive drain-source avalanche current | $V_{GS} = 10\text{ V}; V_{sup} \leq 25\text{ V}; R_{GS} = 50\text{ }\Omega; T_{j(init)} = 25\text{ °C}$; unclamped; see Figure 4 | - | 10.3 | A |



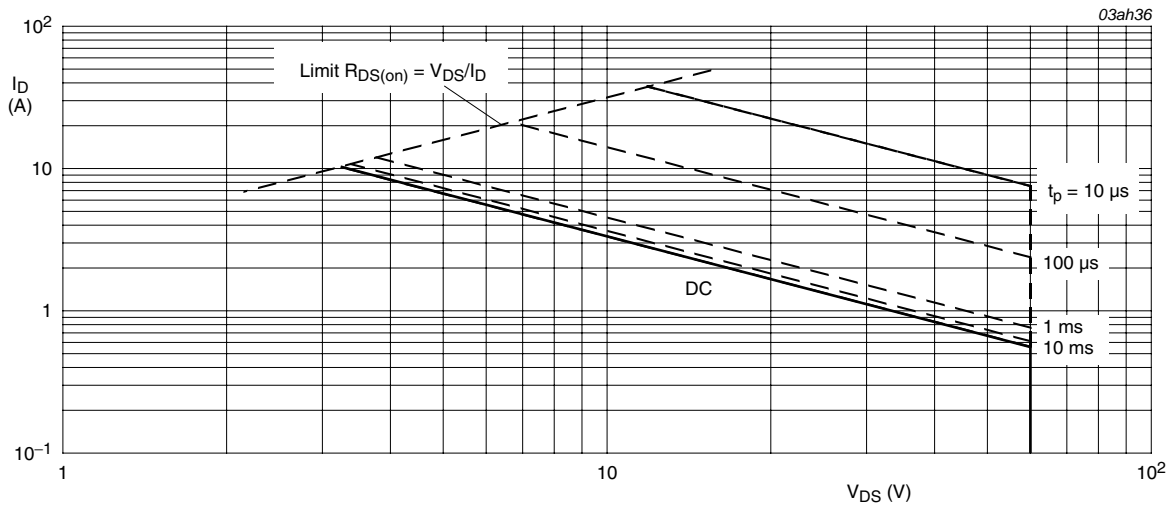
$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



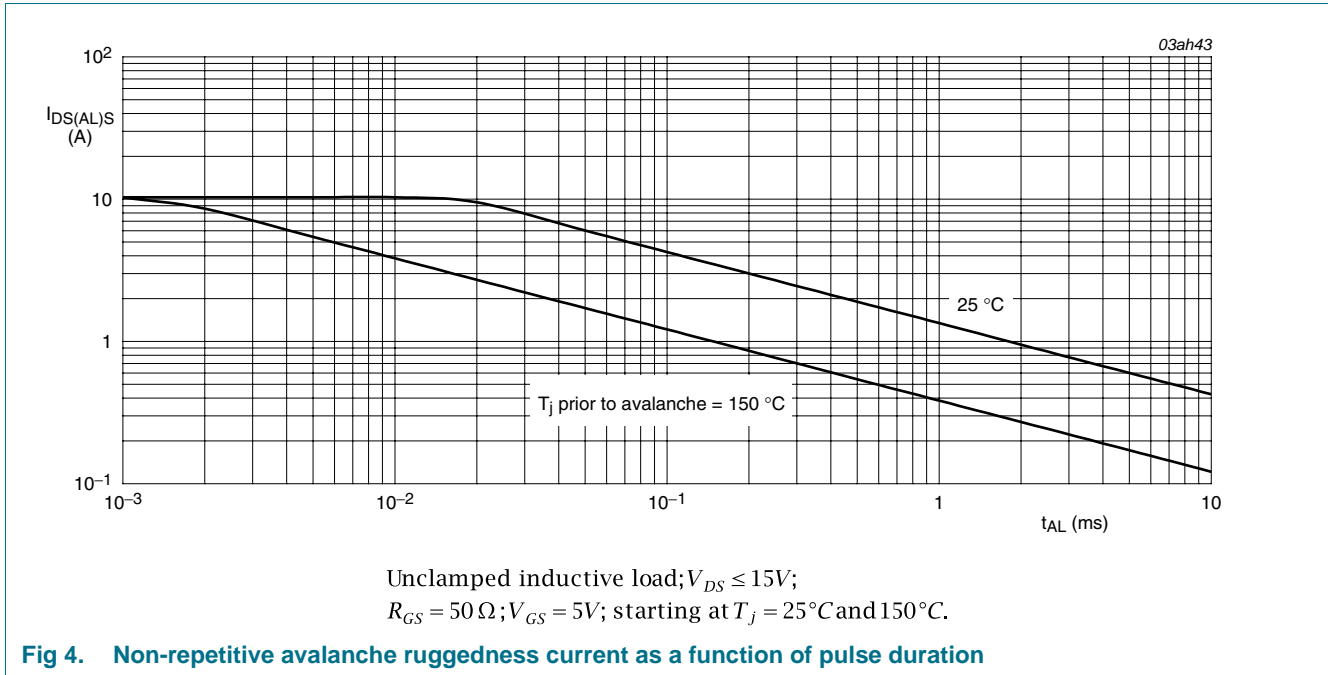
$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25^\circ\text{C}; I_{DM}$ is single pulse

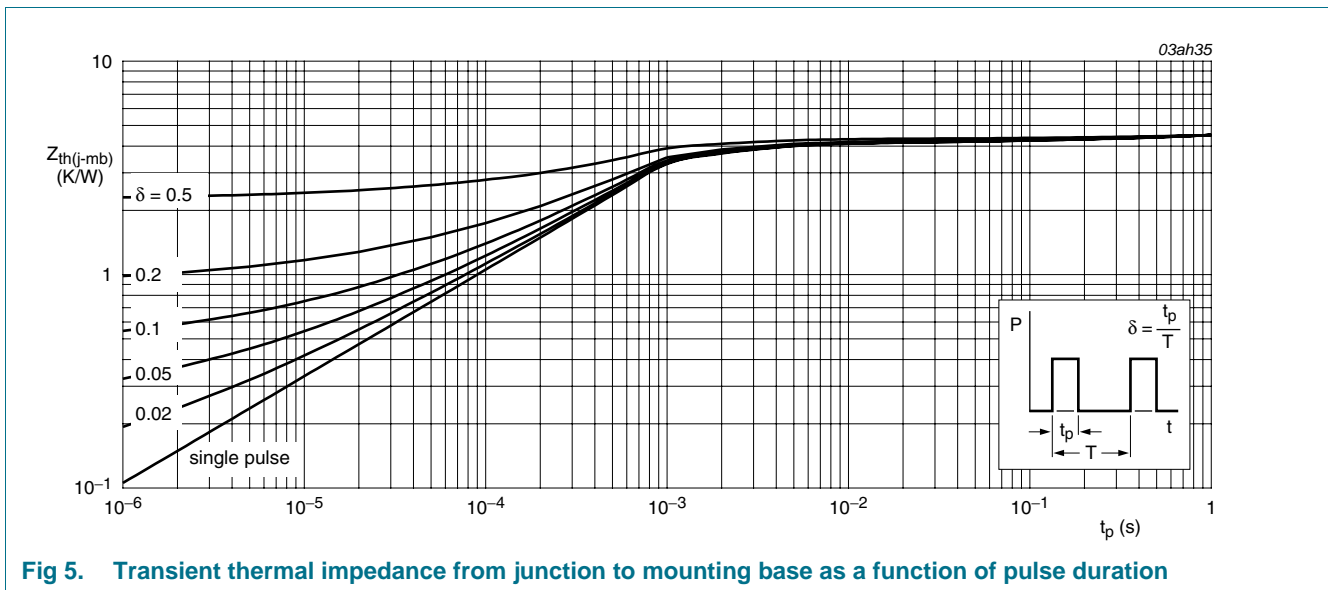
Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



5. Thermal characteristics

Table 5. Thermal characteristics

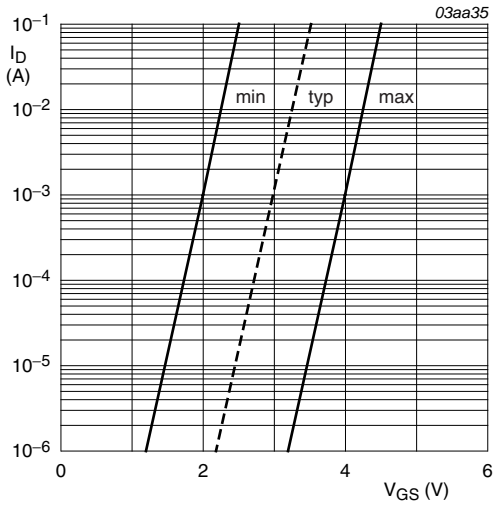
| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|----------------|---|------------------------------|-----|-----|-----|------|
| $R_{th(j-mb)}$ | thermal resistance from junction to mounting base | see Figure 5 | - | - | 4.5 | K/W |
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | vertical in still air | - | 60 | - | K/W |



6. Characteristics

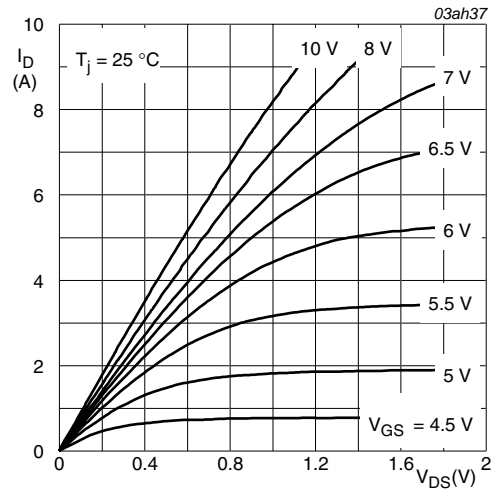
Table 6. Characteristics

| Symbol | Parameter | Conditions | Min | Typ | Max | Unit |
|--------------------------------|----------------------------------|---|-----|------|-----|---------------|
| Static characteristics | | | | | | |
| $V_{(BR)DSS}$ | drain-source breakdown voltage | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$ | 55 | - | - | V |
| | | $I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | 60 | - | - | V |
| $V_{GS(th)}$ | gate-source threshold voltage | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 9 | 1 | - | - | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see Figure 9 | - | - | 6 | V |
| | | $I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 9 | 2 | 3 | 4 | V |
| I_{DSS} | drain leakage current | $V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$ | - | - | 500 | μA |
| | | $V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 0.05 | 10 | μA |
| I_{GSS} | gate leakage current | $V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 10 | 100 | nA |
| | | $V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 10 | 100 | nA |
| $R_{DS(on)}$ | drain-source on-state resistance | $V_{GS} = 10 \text{ V}; I_D = 5.5 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see Figure 10 and 11 | - | 250 | 315 | m Ω |
| | | $V_{GS} = 10 \text{ V}; I_D = 5.5 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 10 and 11 | - | 120 | 150 | m Ω |
| Dynamic characteristics | | | | | | |
| $Q_{G(tot)}$ | total gate charge | $I_D = 10 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 12 | - | 5.8 | - | nC |
| Q_{GS} | gate-source charge | | - | 1.5 | - | nC |
| Q_{GD} | gate-drain charge | | - | 3.2 | - | nC |
| C_{iss} | input capacitance | $V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see Figure 13 | - | 190 | 250 | pF |
| C_{oss} | output capacitance | | - | 55 | 80 | pF |
| C_{rss} | reverse transfer capacitance | | - | 40 | 50 | pF |
| $t_{d(on)}$ | turn-on delay time | $V_{DS} = 30 \text{ V}; R_L = 2.7 \text{ } \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 5.6 \text{ } \Omega; T_j = 25 \text{ }^\circ\text{C}$ | - | 3 | 10 | ns |
| t_r | rise time | | - | 26 | 35 | ns |
| $t_{d(off)}$ | turn-off delay time | | - | 8 | 15 | ns |
| t_f | fall time | | - | 10 | 20 | ns |
| Source-drain diode | | | | | | |
| V_{SD} | source-drain voltage | $I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ see Figure 14 | - | 1.1 | 1.5 | V |
| t_{rr} | reverse recovery time | $I_S = 10 \text{ A}; di_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$ $V_{DS} = 25 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$ | - | 32 | - | ns |
| Q_r | recovered charge | | - | 50 | - | nC |



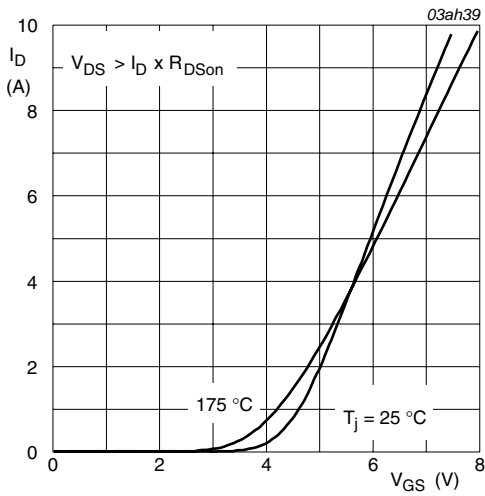
$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

Fig 6. Sub-threshold drain current as a function of gate-source voltage



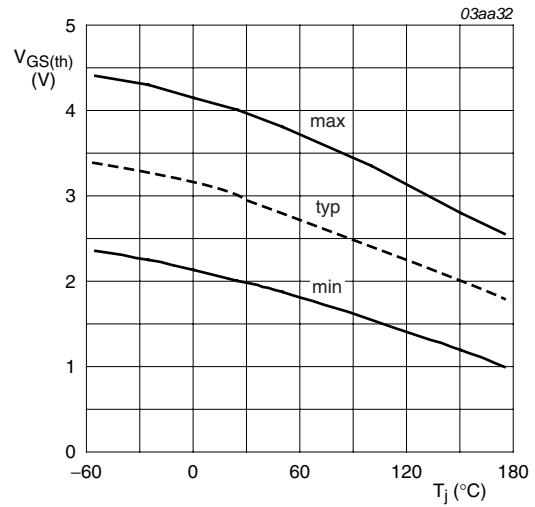
$T_j = 25^\circ\text{C}$

Fig 7. Output characteristics: drain current as a function of drain-source voltage; typical values



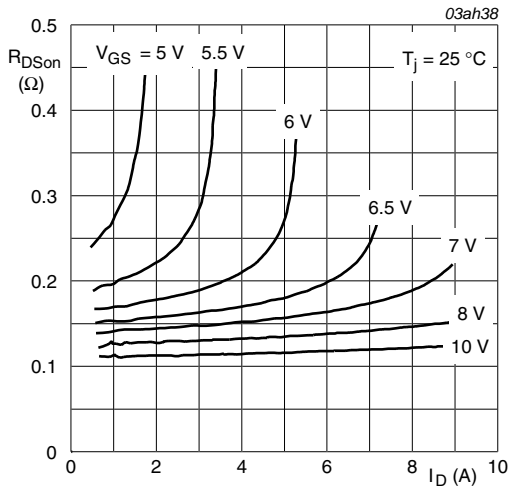
$T_j = 25^\circ\text{C}$ and $175^\circ\text{C}; V_{DS} > I_D \times R_{DSon}$

Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values



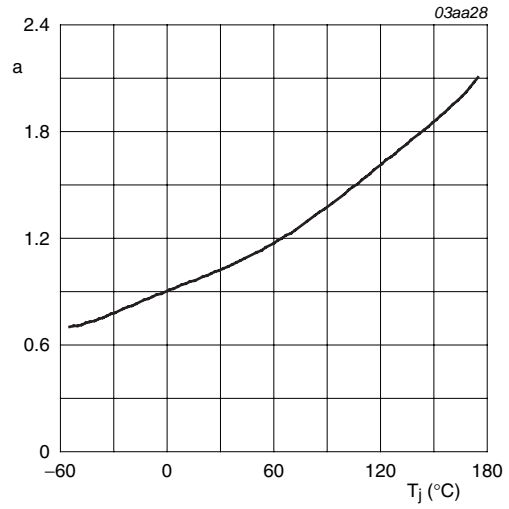
$I_D = 1\text{mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature



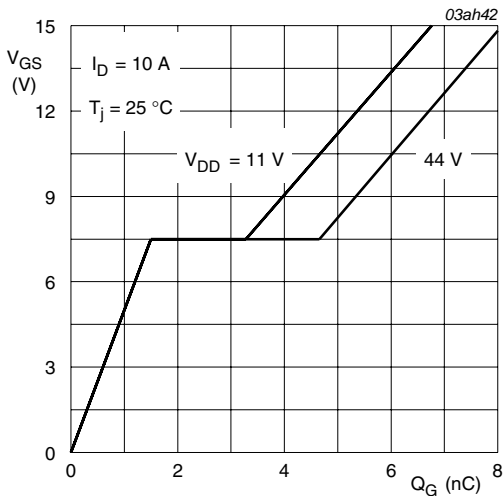
$T_j = 25^\circ\text{C}$

Fig 10. Drain-source on-state resistance as a function of drain current; typical values



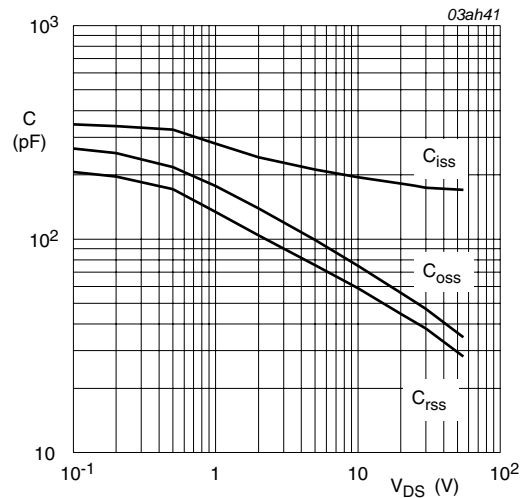
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature



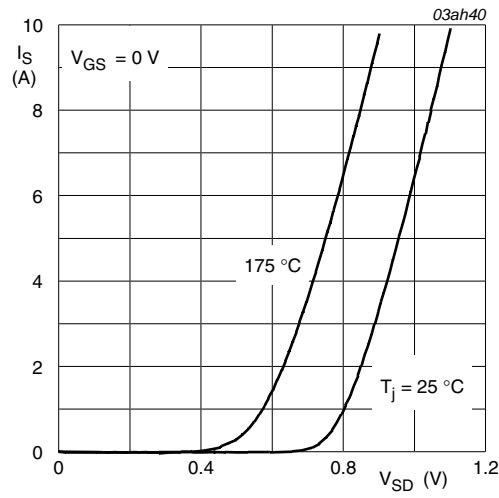
$I_D = 10\text{A}; V_{DD} = 11\text{V and } 44\text{V}$

Fig 12. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0\text{V}; f = 1\text{MHz}$

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values



$T_j = 25^\circ C$ and $175^\circ C; V_{GS} = 0V$

Fig 14. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

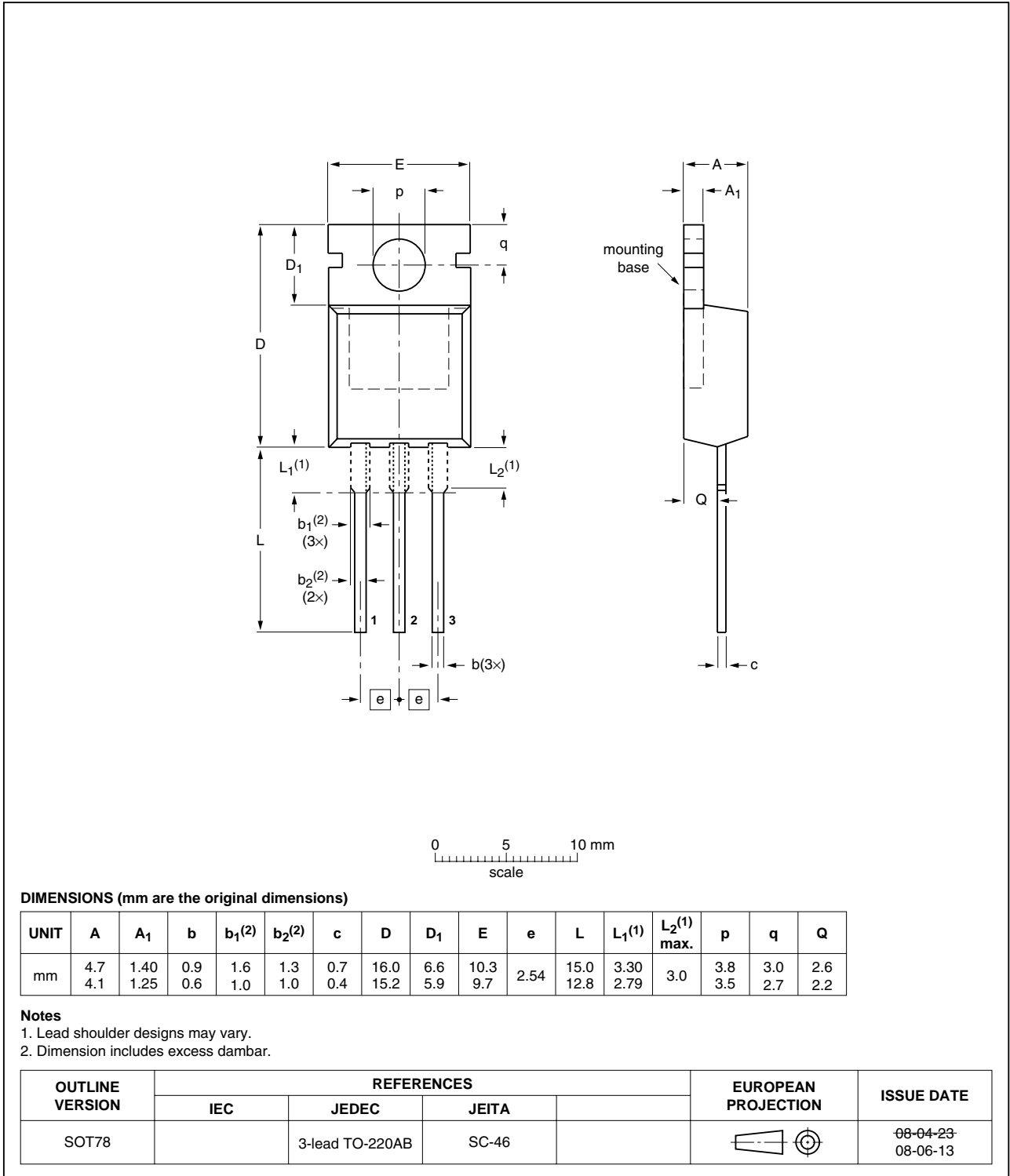


Fig 15. Package outline SOT78 (TO-220AB)

8. Revision history

Table 7. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes |
|-------------------------------------|--------------|--|---------------|-----------------|
| PHP3055E_7 | 20100226 | Product data sheet | - | PHP_PHD3055E-06 |
| Modifications: | | <ul style="list-style-type: none">• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.• Legal texts have been adapted to the new company name where appropriate.• Typenumber PHP3055E separated from datasheet PHP_PHD3055E-06. | | |
| PHP_PHD3055E-06 (9397 750 09354) | 20020325 | Product data | - | - |

9. Legal information

9.1 Data sheet status

| Document status ^{[1][2]} | Product status ^[3] | Definition |
|-----------------------------------|-------------------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

[3] The product status of device(s) described in this document may have changed since this document was published and may differ in case of multiple devices. The latest product status information is available on the Internet at URL <http://www.nxp.com>.

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Date of release: 26 February 2010

Document identifier: PHP3055E_7